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Specification

Surface Shape Recognizing Sensor Device

Technical Field

5 The present invention relates to a surface shape recognizing sensor device and, more particularly, to a surface shape recognizing sensor device which senses fine ridges and valleys of, e.g., fingerprints of humans and noseprints of animals.

10 Background Art

 A sensor which particularly senses fingerprints is reported as a sensor for recognizing a surface shape having fine ridges and valleys. Also, as a technique for detecting fingerprint patterns, a
15 capacitive fingerprint sensor using the LSI fabrication technique is proposed. Examples of the capacitive fingerprint sensor are described in reference 1 (Japanese Patent Laid-Open No. 2000-346608) and reference 2 ("A Robust, 1.8 V 250 μ W Direct-Contact 500
20 dpi Fingerprint Sensor", ISSCC DIGEST OF TECHNICAL PAPERS, February 1998, pp. 284-285).

 As shown in Fig. 18, each of these capacitive fingerprint sensors is formed as a sensor cell array 2 in which sensor cells 1 are two-dimensionally arrayed on
25 an LSI chip, and detects the capacitance formed between a sensor electrode of each sensor cell 1 and the skin of a finger 3 which comes in contact with the sensor

electrode via an insulating passivation film, thereby sensing the pattern of ridges and valleys of the fingerprint. Since the value of the capacitance changes in accordance with a ridge or valley of a fingertip skin surface, a ridge or valley of a fingertip skin surface can be sensed by detecting this fine capacitance difference.

As shown in Fig. 19, a sensor electrode 101 is incorporated into each sensor cell 1 of the sensor cell array 2.

A surface shape recognizing sensor device as the first prior art using the principle of the capacitive fingerprint sensor shown in Fig. 18 will be explained with reference to Fig. 20. In the surface shape recognizing sensor device shown in Fig. 20, each sensor cell 1 comprises a detecting element 10, signal generating circuit 11, switch SW1, and detection circuit 12.

The detecting element 10 includes an insulating layer 100 on a substrate, a sensor electrode 101 formed on the insulating layer 100, and a passivation film 102 so formed as to cover the sensor electrode 101.

The signal generating circuit 11 includes a switch SW2 which generates a voltage signal corresponding to a capacitance C_f formed between the sensor electrode 101 and the skin of a finger 3 in

contact with the passivation film 102, and a current source 110. The detection circuit 12 detects the voltage signal from the signal generating circuit 11. The switch SW1 supplies a potential V_p to a node N1 as a
5 connecting point between the sensor electrode 101 of the detecting element 10 and the output terminal of the signal generating circuit 11. Note that C_p in Fig. 20 denotes a parasitic capacitance.

Since the capacitance C_f is determined by the
10 distance between the sensor electrode 101 and the skin of the finger 3, the value of C_f changes in accordance with a ridge or valley of a fingerprint. Accordingly, a voltage signal corresponding to a ridge or valley of the finger 3 is output from the signal generating circuit 11
15 to the node N1. This voltage signal is detected as a signal reflecting the ridge or valley of the fingerprint by the detection circuit 12, and as a consequence the fingerprint pattern is detected.

A normal operation of the surface shape
20 recognizing sensor device shown in Fig. 20 will be explained with reference to Figs. 21A to 21D. The surface of the finger 3 is connected to the ground potential (GND) via a resistance R_f of the finger 3. Assume that $R_f = 0 \Omega$. Accordingly, the potential of the
25 finger surface, i.e., the potential at a node N2 is held at the ground potential (Fig. 21D).

Initially, a control signal P for controlling

opening/closure of the switch SW1 is Low level
(Fig. 21A). A control signal S1 for controlling
opening/closure of the switch SW2 is also Low level
(Fig. 21B). Therefore, both the switches SW1 and SW2
5 are open. In this case, the potential at the node N1 is
equal to or lower than the potential Vp (Fig. 21C).

In this state, if the control signal P changes
from Low level to High level at time t1 in Fig. 21A, the
switch SW1 is closed and turned on, and consequently the
10 potential at the node N1 is precharged to the potential
Vp (Fig. 21C).

After the precharge is completed, the control
signal P changes to Low level at time t2 in Fig. 21A,
and simultaneously the control signal S1 changes to High
15 level as shown in Fig. 21B. Accordingly, the switch SW1
is turned off, the switch SW2 is turned on, and the
electric charge stored in the node N1 is extracted by
the current source 110. As a consequence, the potential
(voltage signal) at the node N1 lowers (Fig. 21C).

20 Letting Δt be a High-level period of the control signal
S1, a potential drop ΔV of the node N1 from the
potential Vp when Δt has elapsed is given by

$$\Delta V = I\Delta t / (C_f + C_p) \quad \dots(1)$$

where I is the current value of the current source 110,
25 and Cp is a parasitic capacitance.

Since the electric current I, period Δt , and
parasitic capacitance Cp are constant, the potential

drop ΔV is determined by the capacitance C_f . The capacitance C_f is determined by the distance between the sensor electrode 101 of the detecting element 10 and the skin of the finger 3, so the value of the capacitance C_f changes in accordance with a ridge or valley of a fingertip skin surface. Accordingly, the change in magnitude of the potential drop ΔV reflects a ridge or valley of a fingertip skin surface. That is, letting C_{fv} be the capacitance formed between a valley of a fingertip skin surface and the sensor electrode 101 and C_{fr} be the capacitance formed between a ridge of a fingertip skin surface and the sensor electrode 101, a difference ΔV_i between a voltage signal corresponding to a valley of a fingertip skin surface and a voltage signal corresponding to a ridge of a fingertip skin surface is given by

$$\Delta V_i = I\Delta t / (C_{fv} + C_p) - I\Delta t / (C_{fr} + C_p) \quad \dots(2)$$

Since, therefore, the voltage signal detected by the detection circuit 12 of each sensor cell is a signal reflecting a ridge or valley of a fingertip skin surface, ridges and valleys of a fingertip skin surface can be discriminated by outputs from a plurality of sensor cells.

The surface of the finger 3, however, is connected to the ground potential via the resistance R_f of the finger 3, so no sufficiently large voltage difference ΔV_i can be obtained in some cases if the

resistance R_f is high because, e.g., the finger 3 is dry. The operation of the surface shape recognizing sensor device when $R_f \gg 0$ will be explained with reference to Figs. 22A to 22D.

5 The basic operation timings in Figs. 22A to 22D are the same as in Figs. 21A to 21D. On a ridge of a fingerprint, however, the potential of the finger surface, i.e., the potential at the node N2 cannot hold the ground potential and fluctuates as shown in Fig. 22D
10 with the potential change at the node N1 shown in Fig. 22C. Consequently, the value of the capacitance C_f formed between the ridge of the fingertip skin surface and the sensor electrode 101 effectively decreases ($C_f = \alpha C_{fr}$, $\alpha < 1$), and as a result the voltage difference ΔV_i
15 ($= I\Delta t / (C_{fv} + C_p) - I\Delta t / (\alpha \cdot C_{fr} + C_p)$) decreases as shown in Fig. 22C. This makes it difficult for the surface shape recognizing sensor device shown in Fig. 20 to discriminate between the ridge and valley patterns of a fingerprint image, and consequently no clear fingerprint
20 image pattern can be obtained.

A surface shape recognizing sensor device as the second prior art using the principle of the capacitive fingerprint sensor shown in Fig. 18 will be explained with reference to Fig. 23.

25 This surface shape recognizing sensor device differs from the example shown in Fig. 20 in the arrangement of a signal generating circuit 13. The

signal generating circuit 13 includes a switch SW3 which selects and outputs a power supply potential VDD or ground potential GND, and a capacitive element Cs formed between the output terminal of the switch SW3 and a node N1. The signal generating circuit 13 extracts an electric charge from the node N1 by charging/discharging the capacitive element Cs, and the charge amount to be extracted is controlled by the capacitance value of Cs and a driving voltage Vs of Cs. In this device, the charge amount to be extracted from the node N1 is controlled by setting the driving voltage Vs shown in Fig. 23 at the power supply potential VDD ($VDD > 0$) or ground potential GND via the switch SW3.

A normal operation of the surface shape recognizing sensor device shown in Fig. 23 will be explained with reference to Figs. 24A to 24D. The surface of a finger 3 is connected to the ground potential via a resistance Rf of the finger 3. Assume that $Rf = 0 \Omega$. Accordingly, the potential of the finger surface, i.e., the potential at a node N2 is held at the ground potential (Fig. 24D).

At time t1 in Fig. 24A, the switch SW1 is closed by changing the potential of a control signal P to High level, thereby precharging a potential Vp in the node N1. In this case, the driving voltage Vs of the capacitive element Cs in the signal generating circuit 13 is set at VDD. After that, at time t2 in Fig. 24A,

the switch SW is opened by changing the potential of the control signal P to Low level. At the same time, as shown in Fig. 24B, the driving voltage Vs of the capacitive element Cs is decreased by ΔVs from VDD and set at GND, thereby extracting the electric charge from the node N1 to generate a voltage signal to a detection circuit 12.

A change amount ΔV of the voltage signal to be applied to the detection circuit 12 is give by

$$\Delta V = \Delta V_s / \{1 + (C_f + C_p) / C_s\} \quad \dots(3)$$

A difference ΔVi between a voltage signal corresponding to a valley of a fingertip skin surface and a voltage signal corresponding to a ridge of a fingertip skin surface is given by

$$\Delta V_i = \Delta V_s / \{1 + (C_{fv} + C_p) / C_s\} - \Delta V_s / \{1 + (C_{fr} + C_p) / C_s\} \quad \dots(4)$$

Since, therefore, the voltage signal detected by the detection circuit 12 of each sensor cell is a signal reflecting a ridge or valley of a fingerprint, ridges and valleys of a fingertip skin surface can be discriminated by outputs from a plurality of sensor cells.

The surface of the finger 3, however, is connected to the ground potential via the resistance Rf of the finger 3, so no sufficiently large voltage difference ΔVi can be obtained in some cases if the resistance Rf is high because, e.g., the finger 3 is

dry. The operation of the surface shape recognizing sensor device when $R_f \gg 0$ will be explained with reference to Figs. 25A to 25D.

The basic operation timings in Figs. 25A to 25D are the same as in Figs. 24A to 24D. On a ridge of a fingertip skin surface, however, the potential of the finger surface, i.e., the potential at the node N2 cannot hold the ground potential and fluctuates as shown in Fig. 25D with the potential change at the node N1 shown in Fig. 25C. Consequently, the value of the capacitance C_f formed between the ridge of the fingertip skin surface and the sensor electrode 101 effectively decreases ($C_f = \alpha C_{fr}$, $\alpha < 1$), and as a result the voltage difference $\Delta V_i (= \Delta V_s / \{1 + (C_{fv} + C_p) / C_s\} - \Delta V_s / \{1 + (\alpha C_{fr} + C_p) / C_s\})$ decreases as shown in Fig. 25C. This makes it difficult for the surface shape recognizing sensor device shown in Fig. 23 to discriminate between the ridge and valley patterns of a fingerprint image, and as a consequence no clear fingerprint image pattern can be obtained.

Disclosure of Invention

Problem to be Solved by the Invention

As described above, when the conventional surface shape recognizing sensor device is used as a fingerprint sensor for fingerprint authentication, if the resistance R_f of the finger 3 is high, it becomes difficult to discriminate between the ridge and valley

patterns of a fingerprint image, so no clear fingerprint image can be obtained any longer. As a consequence, when a fingerprint image deteriorates due to the resistance R_f of the finger 3, the authentication ratio
5 decreases.

The present invention has been made to solve this problem, and has as its object to provide a surface shape recognizing sensor device capable of increasing the sensitivity of detection of a capacitance
10 corresponding to a ridge or valley of the surface of an object to be recognized, e.g., a fingerprint.

Means for Solving the Problem

To achieve the above object, the present invention is characterized by comprising a plurality of
15 sensor cells which are two-dimensionally arranged, detect capacitances corresponding to ridges and valleys of a surface of an object to be recognized, and output signals corresponding to the capacitances, and a signal processor which calculates a surface shape of the object
20 on the basis of the signals input from the sensor cells, the sensor cell comprising a substrate, a first electrode formed on the substrate, a signal output unit which outputs a signal corresponding to a capacitance formed between the first electrode and the surface of
25 the object, a second electrode formed on the substrate so as to be insulated and isolated from the first electrode, and a potential controller which controls a

potential of the surface of the object via a capacitance formed between the second electrode and the surface of the object by controlling a potential of the second electrode.

5 Effects of the Invention

The present invention controls the potential of the surface of an object to be recognized via the capacitance formed between the second electrode and the surface of the object by controlling the potential of the second electrode by using the potential controller. When the resistance of the object is high, therefore, the surface potential of the object can be controlled so as not to fluctuate with the potential change of the first electrode. This makes it possible to increase the sensitivity of detection of the capacitance formed between the first electrode and the surface of the object. As a consequence, ridges and valleys of the surface of the object can be clearly discriminated by outputs from a plurality of sensor cells. Especially when the present invention is used as a fingerprint sensor for fingerprint authentication, it is possible to prevent deterioration of a fingerprint image caused by the surface resistance of the finger, and obtain an effect of preventing a decrease in authentication ratio.

25 Brief Description of Drawings

Fig. 1 is a block diagram showing the overall arrangement of a surface shape recognizing sensor device

according to the first embodiment of the present invention;

Fig. 2 is a block diagram showing the arrangement of the surface shape recognizing sensor device according to the first embodiment of the present invention;

Fig. 3A is a plan view showing an example of the layout pattern of sensor electrodes and high-sensitivity electrodes in a sensor cell array of the surface shape recognizing sensor device shown in Fig. 1;

Fig. 3B is a plan view showing another example of the layout pattern of the sensor electrodes and high-sensitivity electrodes in the sensor cell array of the surface shape recognizing sensor device shown in Fig. 1;

Fig. 4A is one of timing charts for explaining an example of the operation of the surface shape recognizing sensor device shown in Fig. 1 when the resistance of a finger is high, in which the change in control signal P with time is shown;

Fig. 4B is one of the timing charts for explaining the example of the operation of the surface shape recognizing sensor device shown in Fig. 1 when the resistance of a finger is high, in which the change in control signal S1 with time is shown;

Fig. 4C is one of the timing charts for

explaining the example of the operation of the surface shape recognizing sensor device shown in Fig. 1 when the resistance of a finger is high, in which the change in potential at a node N1 is shown;

5 Fig. 4D is one of the timing charts for explaining the example of the operation of the surface shape recognizing sensor device shown in Fig. 1 when the resistance of a finger is high, in which the change in potential at a node N2 is shown;

10 Fig. 4E is one of the timing charts for explaining the example of the operation of the surface shape recognizing sensor device shown in Fig. 1 when the resistance of a finger is high, in which the change in potential at a node N3 is shown;

15 Fig. 5 is a block diagram showing an implementation example of a potential control circuit of the first embodiment of the present invention;

 Fig. 6A is one of timing charts for explaining an example of the operation of the surface shape
20 recognizing sensor device shown in Fig. 1 when the resistance of a finger is high, in which the change in control signal P with time is shown;

 Fig. 6B is one of the timing charts for explaining the example of the operation of the surface
25 shape recognizing sensor device shown in Fig. 1 when the resistance of a finger is high, in which the change in control signal S1 with time is shown;

Fig. 6C is one of the timing charts for explaining the example of the operation of the surface shape recognizing sensor device shown in Fig. 1 when the resistance of a finger is high, in which the change in potential at the node N1 is shown;

Fig. 6D is one of the timing charts for explaining the example of the operation of the surface shape recognizing sensor device shown in Fig. 1 when the resistance of a finger is high, in which the change in potential at the node N2 is shown;

Fig. 6E is one of the timing charts for explaining the example of the operation of the surface shape recognizing sensor device shown in Fig. 1 when the resistance of a finger is high, in which the change in potential at the node N3 is shown;

Fig. 7 is a block diagram showing the arrangement of a surface shape recognizing sensor device according to the second embodiment of the present invention;

Fig. 8A is one of timing charts for explaining an example of the operation of the surface shape recognizing sensor device shown in Fig. 7 when the resistance of a finger is high, in which the change in control signal P with time is shown;

Fig. 8B is one of the timing charts for explaining the example of the operation of the surface shape recognizing sensor device shown in Fig. 7 when the

resistance of a finger is high, in which the change in driving voltage V_s of a capacitive element C_s with time is shown;

Fig. 8C is one of the timing charts for
5 explaining the example of the operation of the surface shape recognizing sensor device shown in Fig. 7 when the resistance of a finger is high, in which the change in potential at a node N1 is shown;

Fig. 8D is one of the timing charts for
10 explaining the example of the operation of the surface shape recognizing sensor device shown in Fig. 7 when the resistance of a finger is high, in which the change in potential at a node N2 is shown;

Fig. 8E is one of the timing charts for
15 explaining the example of the operation of the surface shape recognizing sensor device shown in Fig. 7 when the resistance of a finger is high, in which the change in potential at a node N3 is shown;

Fig. 9A is a block diagram showing an
20 implementation example of a potential control circuit of the second embodiment of the present invention;

Fig. 9B is a block diagram showing another implementation example of the potential control circuit of the second embodiment of the present invention;

25 Fig. 10A is one of timing charts for explaining another example of the operation of the surface shape recognizing sensor device shown in Fig. 7

when the resistance of a finger is high, in which the change in control signal P with time is shown;

Fig. 10B is one of the timing charts for explaining the other example of the operation of the surface shape recognizing sensor device shown in Fig. 7 when the resistance of a finger is high, in which the change in driving voltage Vs of the capacitive element Cs with time is shown;

Fig. 10C is one of the timing charts for explaining the other example of the operation of the surface shape recognizing sensor device shown in Fig. 7 when the resistance of a finger is high, in which the change in potential at the node N1 is shown;

Fig. 10D is one of the timing charts for explaining the other example of the operation of the surface shape recognizing sensor device shown in Fig. 7 when the resistance of a finger is high, in which the change in potential at the node N2 is shown;

Fig. 10E is one of the timing charts for explaining the other example of the operation of the surface shape recognizing sensor device shown in Fig. 7 when the resistance of a finger is high, in which the change in potential at the node N3 is shown;

Fig. 11 is a block diagram showing an implementation example of a potential control circuit of a surface shape recognizing sensor device according to the third embodiment of the present invention;

Fig. 12A is one of timing charts for explaining the operation of the surface shape recognizing sensor device using the potential control circuit shown in Fig. 11 when the resistance of a finger is high, in which the change in control signal P with time is shown;

Fig. 12B is one of the timing charts for explaining the operation of the surface shape recognizing sensor device using the potential control circuit shown in Fig. 11 when the resistance of a finger is high, in which the change in control signal S1 with time is shown;

Fig. 12C is one of the timing charts for explaining the operation of the surface shape recognizing sensor device using the potential control circuit shown in Fig. 11 when the resistance of a finger is high, in which the change in potential at a node N1 is shown;

Fig. 12D is one of the timing charts for explaining the operation of the surface shape recognizing sensor device using the potential control circuit shown in Fig. 11 when the resistance of a finger is high, in which the change in potential at a node N2 is shown;

Fig. 12E is one of the timing charts for explaining the operation of the surface shape recognizing sensor device using the potential control

circuit shown in Fig. 11 when the resistance of a finger is high, in which the change in potential at a node N3 is shown;

Fig. 13A is a block diagram showing an
5 implementation example of a potential control circuit of a surface shape recognizing sensor device according to the fourth embodiment of the present invention;

Fig. 13B is a block diagram showing another
implementation example of the potential control circuit
10 of the surface shape recognizing sensor device according to the fourth embodiment of the present invention;

Fig. 14A is one of timing charts for
explaining the operation of the surface shape
recognizing sensor device using the potential control
15 circuit shown in Fig. 13 when the resistance of a finger is high, in which the change in control signal P with time is shown;

Fig. 14B is one of the timing charts for
explaining the operation of the surface shape
20 recognizing sensor device using the potential control circuit shown in Fig. 13 when the resistance of a finger is high, in which the change in driving voltage Vs of the capacitive element Cs with time is shown;

Fig. 14C is one of the timing charts for
25 explaining the operation of the surface shape recognizing sensor device using the potential control circuit shown in Fig. 13 when the resistance of a finger

is high, in which the change in potential at a node N1 is shown;

Fig. 14D is one of the timing charts for explaining the operation of the surface shape

5 recognizing sensor device using the potential control circuit shown in Fig. 13 when the resistance of a finger is high, in which the change in potential at a node N2 is shown;

Fig. 14E is one of the timing charts for

10 explaining the operation of the surface shape

recognizing sensor device using the potential control circuit shown in Fig. 13 when the resistance of a finger is high, in which the change in potential at a node N3 is shown;

15 Fig. 15 is a plan view showing the layout pattern of sensor electrodes and high-sensitivity electrodes in a sensor cell array according to the fifth embodiment of the present invention;

Fig. 16 is a plan view showing the layout
20 pattern of sensor electrodes and high-sensitivity electrodes in a sensor cell array according to the sixth embodiment of the present invention;

Fig. 17A is a sectional view showing examples of the formation positions of a sensor electrode and
25 high-sensitivity electrode in a sensor cell array according to the seventh embodiment of the present invention;

Fig. 17B is a sectional view showing other examples of the formation positions of the sensor electrode and high-sensitivity electrode in the sensor cell array according to the seventh embodiment of the present invention;

Fig. 18 is a perspective view of a conventional capacitive fingerprint sensor in which sensor cells are formed into a lattice shape;

Fig. 19 is a plan view showing the layout pattern of sensor electrodes in a sensor cell array shown in Fig. 18;

Fig. 20 is a block diagram showing the arrangement of a surface shape recognizing sensor device as the first prior art;

Fig. 21A is one of timing charts for explaining a normal operation of the surface shape recognizing sensor device shown in Fig. 20, in which the change in control signal P with time is shown;

Fig. 21B is one of the timing charts for explaining the normal operation of the surface shape recognizing sensor device shown in Fig. 20, in which the change in control signal S1 with time is shown;

Fig. 21C is one of the timing charts for explaining the normal operation of the surface shape recognizing sensor device shown in Fig. 20, in which the change in potential at a node N1 is shown;

Fig. 21D is one of the timing charts for

explaining the normal operation of the surface shape recognizing sensor device shown in Fig. 20, in which the change in potential at a node N2 is shown;

Fig. 22A is one of timing charts for
5 explaining the operation of the surface shape recognizing sensor device shown in Fig. 20 when the resistance of a finger is high, in which the change in control signal P with time is shown;

Fig. 22B is one of the timing charts for
10 explaining the operation of the surface shape recognizing sensor device shown in Fig. 20 when the resistance of a finger is high, in which the change in control signal S1 with time is shown;

Fig. 22C is one of the timing charts for
15 explaining the operation of the surface shape recognizing sensor device shown in Fig. 20 when the resistance of a finger is high, in which the change in potential at the node N1 is shown;

Fig. 22D is one of the timing charts for
20 explaining the operation of the surface shape recognizing sensor device shown in Fig. 20 when the resistance of a finger is high, in which the change in potential at the node N2 is shown;

Fig. 23 is a block diagram showing the
25 arrangement of a surface shape recognizing sensor device as the second prior art;

Fig. 24A is one of timing charts for

explaining a normal operation of the surface shape
recognizing sensor device shown in Fig. 23, in which the
change in control signal P with time is shown;

Fig. 24B is one of the timing charts for
5 explaining the normal operation of the surface shape
recognizing sensor device shown in Fig. 23, in which the
change in driving voltage Vs of a capacitive element Cs
with time is shown;

Fig. 24C is one of the timing charts for
10 explaining the normal operation of the surface shape
recognizing sensor device shown in Fig. 23, in which the
change in potential at a node N1 is shown;

Fig. 24D is one of the timing charts for
explaining the normal operation of the surface shape
15 recognizing sensor device shown in Fig. 23, in which the
change in potential at a node N2 is shown;

Fig. 25A is one of timing charts for
explaining the operation of the surface shape
recognizing sensor device shown in Fig. 23 when the
20 resistance of a finger is high, in which the change in
control signal P with time is shown;

Fig. 25B is one of the timing charts for
explaining the operation of the surface shape
recognizing sensor device shown in Fig. 23 when the
25 resistance of a finger is high, in which the change in
driving voltage Vs of the capacitive element Cs with
time is shown;

Fig. 25C is one of the timing charts for explaining the operation of the surface shape recognizing sensor device shown in Fig. 23 when the resistance of a finger is high, in which the change in potential at the node N1 is shown; and

Fig. 25D is one of the timing charts for explaining the operation of the surface shape recognizing sensor device shown in Fig. 23 when the resistance of a finger is high, in which the change in potential at the node N2 is shown.

Best Mode for Carrying Out the Invention

The principal characteristic feature of a surface shape recognizing sensor device of the present invention is to have a means for increasing the sensitivity of detection of a signal (capacitance) corresponding to a ridge or valley of a surface shape. The differences from the prior art are that each sensor cell of the surface shape recognizing sensor device has a second electrode in addition to a sensor electrode, and the surface potential of a surface shape is controlled by controlling the potential of the second electrode.

Embodiments of the present invention will be described in detail below with reference to the accompanying drawings.

[First Embodiment]

As shown in Fig. 1, a surface shape

recognizing sensor device according to the first
embodiment of the present invention has a sensor cell
array 2a in which a plurality of sensor cells 1a are
two-dimensionally arrayed, a signal processor 4, and a
5 control signal output unit 5. Each sensor cell 1a
senses a capacitance corresponding to a ridge or valley
of the surface of a finger as an object to be
recognized, and outputs a signal corresponding to the
capacitance to the signal processor 4. The signal
10 processor 4 integrates the input signals from the sensor
cells 1a, and calculates the surface shape of the
finger. The control signal output unit 5 outputs a
control signal S1 to each sensor cell 1a, and controls
the operation of the sensor cell 1a.

15 As shown in Fig. 2, the sensor cell 1a has a
detecting element 10a, signal output unit 16, and finger
surface potential controller 14.

 The detecting element 10a includes an
insulating layer 100 on a substrate, a sensor electrode
20 101 (first electrode) formed on the insulating layer
100, a high-sensitivity electrode 103 (second electrode,
control electrode) formed on the insulating layer 100 so
as to be insulated and isolated from the sensor
electrode 101, and a passivation film 102 so formed as
25 to cover the sensor electrode 101 and high-sensitivity
electrode 103. The surface of the passivation film 102
is planarized.

The signal output unit 16 outputs, as the output from the sensor cell 1a, a signal corresponding to a capacitance C_f formed between the sensor electrode 101 and the skin of a finger 3 in contact with the passivation film 102, and more specifically includes a switch SW1 (charging circuit), signal generating circuit 11, and detection circuit 12. The switch SW1 applies a potential V_p to a node N1 as a connecting point between the sensor electrode 101 of the detecting element 10a and the output terminal of the signal generating circuit 11, thereby storing an electric charge. The signal generating circuit 11 generates a voltage signal corresponding to the capacitance C_f formed between the skin of the finger 3 and the sensor electrode 101. The signal generating circuit 11 includes a first current source 110 for removing the electric charge from the node N1, and a switch SW2 (first switching element) which is placed between the current source 110 and the node N1 and generates the voltage signal by electrically connecting the current source 110 and node N1 for only a predetermined time after the electric charge is stored in the node N1. The detection circuit 12 detects the voltage signal from the signal generating circuit 11 after the electric charge is stored in the node N1, and outputs the signal as the output from the signal output unit 16.

The finger surface potential controller 14 has

a potential control circuit 140 which controls the potential of the high-sensitivity electrode 103. The switch SW2 of the signal generating circuit 11 and the potential control circuit 140 are together controlled by the control signal S1 input from the control signal output circuit 5. Note that C_p in Fig. 2 denotes a parasitic capacitance.

The surface shape recognizing sensor device shown in Fig. 2 aims at solving the problem of the conventional surface shape recognizing sensor device shown in Fig. 20, and is obtained by adding the high-sensitivity electrode 103 and potential control circuit 140 to the conventional surface shape recognizing sensor device. Since the potential control circuit 140 controls the potential of the surface (a node N2) of the finger 3 via a capacitance C_c formed between the surface of the finger 3 and the high-sensitivity electrode 103, the potential at the node N2 can be controlled when a resistance R_f is high because, e.g., the finger 3 is dry, thereby increasing the sensitivity of detection of the capacitance C_f .

As shown in Figs. 3A and 3B, each sensor cell 1a of the sensor cell array 2a incorporates the sensor electrode 101 and high-sensitivity electrode 103. The larger the area of the high-sensitivity electrode 103, the more easily the potential of the finger 3 is controlled. However, to increase the detection

sensitivity by arranging both the sensor electrode 101 and high-sensitivity electrode 103 in the limited region of the sensor cell 1a, it is desirable to make the area of the high-sensitivity electrode 103 equal to that of the sensor electrode 101 as shown in Fig. 3A, or make the area of the high-sensitivity electrode 103 smaller than that of the sensor electrode 101 as shown in Fig. 3B.

An example of the operation of the surface shape recognizing sensor device shown in Fig. 1 when $R_f \gg 0$ will be explained below with reference to Figs. 4A to 4E.

Initially, a control signal P for controlling opening/closure of the switch SW1 is Low level (Fig. 4A). The control signal S1 for controlling opening/closure of the switch SW2 is also Low level (Fig. 4B). Accordingly, both the switches SW1 and SW2 are open. In this case, the potential at the node N1 is lower than the potential V_p (Fig. 4C).

In this state, when the control signal P changes from Low level to High level at time t_1 in Fig. 4A, the switch SW1 is closed and turned on, and as a consequence the potential at the node N1 is precharged to the potential V_p (Fig. 4C).

After the precharge is completed, the control signal P changes to Low level at time t_2 in Fig. 4A, and simultaneously the control signal S1 changes to High

level as shown in Fig. 4B. Accordingly, the switch SW1 is turned off, the switch SW2 is turned on, and the electric charge stored in the node N1 is extracted by the current source 110. As a consequence, the potential (voltage signal) at the node N1 decreases (Fig. 4C). The control signal S1 maintains High level for a predetermined period Δt . A potential drop ΔV at the node N1 from the potential V_p when Δt has elapsed is given by equation (1) presented earlier where I is the current value of the current source 110 and C_p is a parasitic capacitance.

In the surface shape recognizing sensor device shown in Fig. 1, unlike in Fig. 22, the potential at a node N3 as a connecting point between the output of the potential control circuit 140 and the high-sensitivity electrode 103 is changed in the opposite direction to the potential change at the node N1 during a period from time t_2 to time t_3 as shown in Fig. 4E. More specifically, the potential at the node N3 is raised. When a ridge of the fingerprint faces the sensor cell 1a, the capacitance C_c formed between the high-sensitivity electrode 103 and the surface of the finger 3 is large. For this reason, the potential at the node N2 can be controlled via the capacitance C_c by controlling the potential at the node N3. By thus controlling the potential at the node N3, therefore, the potential fluctuation at the node N2 during the period

from time t_2 to time 3 can be suppressed as shown in Fig. 4D. This makes it possible to prevent the value of the capacitance C_f from effectively decreasing, and obtain $\alpha = 1$ when $C_f = \alpha \cdot C_{fr}$. Note that when a valley of the fingertip skin surface faces the sensor cell 1a, the capacitance C_c formed between the high-sensitivity electrode 103 and the surface of the finger 3 is small, so the potential at the node N2 is not influenced. Consequently, as shown in Fig. 4C, the magnitude of a difference ΔV_i between a voltage signal corresponding to a valley of the fingertip skin surface and a voltage signal corresponding to a ridge of the fingertip skin surface can be made equal to that shown in Fig. 21C, i.e., that when the resistance R_f of the finger 3 is 0 Ω .

As shown in Fig. 5, for example, the potential control circuit 140 includes a second current source 141 for storing an electric charge in the node N3, and a switch SW4 (second switching element) placed between the node N3 and the current source 141. During a period in which the switch SW4 is turned on, the current source 141 stores an electric charge in the node N3, so the potential at the node N3 rises. The control signal S1 used in the signal generating circuit 11 is also used as a control signal of the switch SW4, so both the switches SW2 and SW4 are turned on when the control signal S1 is High level. The increase in number of control signals

can be prevented by using the control signal S1 for both the switches SW2 and SW4.

Another example of the operation of the surface shape recognizing sensor device shown in Fig. 1
5 when $R_f \gg 0$ will be explained below with reference to Figs. 6A to 6E.

The basic operation is the same as the operation shown in Figs. 4A to 4E. The differences from Figs. 4A to 4E are that, as shown in Fig. 6E, the
10 potential change at the node N3 is larger than that shown in Fig. 4E, and, as shown in Fig. 6D, the potential at the node N2 changes in a direction to increase during the period from time t_2 to time t_3 . This makes it possible to effectively increase the value
15 of the capacitance C_f , and obtain $\alpha > 1$ when $C_f = \alpha \cdot C_{fr}$. Consequently, as shown in Fig. 6C, the magnitude of the difference ΔV_i between the voltage signal corresponding to a valley of the fingertip skin surface and the voltage signal corresponding to a ridge of the fingertip
20 skin surface can be made larger than that shown in Fig. 21C. Since, therefore, it is readily possible to determine whether the voltage signal detected by the detection circuit 12 of each sensor cell corresponds to a ridge or valley of the fingertip skin surface, ridges
25 and valleys of the fingertip skin surface can be clearly discriminated by outputs from a plurality of sensor cells.

In this embodiment as explained above, the potential control circuit 140 controls the potential of the surface (node N2) of the finger 3 via the capacitance Cc formed between the surface of the finger 3 and the high-sensitivity electrode 103, so it is possible to control the potential at the node N2 when the resistance Rf of the finger 3 is high, and increase the sensitivity of detection of the capacitance Cf.

Note that although the potential at the node N3 is changed in accordance with the control signal S1 in this embodiment, what is important is to change the potential at the node N3 in the opposite direction to the potential change at the node N1, so the method is not limited to the use of the control signal S1, and the timing at which the potential at the node N3 is changed is not limited to the period from time t2 to time t3.

Note also that in this embodiment, a signal obtained by storing an electric charge in the node N1 and then removing this electric charge for only a predetermined time is used as the output signal from the sensor cell 1a. However, it is also possible to use, as the output from the sensor cell 1a, a signal obtained by removing the electric charge from the node N1 and then storing an electric charge in the node N1 for only a predetermined time. In this case, the potential Vp shown in Fig. 2 is set at the ground potential to allow the switch SW1 to function as a discharging circuit, and

the current source 110 is connected in the opposite direction to that shown in Fig. 2 so that an electric charge can be stored in the node N1. In this arrangement, if the resistance Rf is high because, e.g., the finger 3 is dry, the potential at the node N2 rises in accordance with the potential change at the node N1 when an electric charge is stored in the node N1. To prevent this, the potential control circuit 140 changes the potential at the node N3 in the opposite direction to the potential change at the node N1. That is, the potential at the node N3 is decreased. More specifically, the current source 141 is connected in the opposite direction to that shown in Fig. 5 so that the potential control circuit 140 can remove the electric charge from the node N3.

[Second Embodiment]

The second embodiment of the present invention will be described below.

A surface shape recognizing sensor device according to the second embodiment of the present invention has a sensor cell array in which a plurality of sensor cells are two-dimensionally arranged, and each sensor cell has a detecting element 10a, signal output unit 17, and finger surface potential controller 15 as shown in Fig. 7. Note that the same reference numerals as in Fig. 2 denote the same parts in Fig. 7.

Similar to Fig. 1, the detecting element 10a

includes an insulating layer 100 on a substrate, a sensor electrode 101, a high-sensitivity electrode 103, and a passivation film 102.

The signal output unit 17 outputs, as the
5 output from a sensor cell 1a, a signal corresponding to a capacitance C_f formed between the sensor electrode 101 and the skin of a finger 3 in contact with the passivation film 102, and more specifically includes a switch SW1 (charging circuit), signal generating circuit
10 13, and detection circuit 12. The switch SW1 applies a potential V_p to a node N1 as a connecting point between the sensor electrode 101 of the detecting element 10a and the output terminal of the signal generating circuit 13, thereby storing an electric charge. The signal
15 generating circuit 13 generates a voltage signal corresponding to the capacitance C_f formed between the skin of the finger 3 and the sensor electrode 101. The signal generating circuit 13 includes a switch SW3
20 of a power supply potential VDD (first potential) and a ground potential GND (second potential) lower than VDD, and a capacitive element C_s formed between the output terminal of the switch SW3 and the node N1. The
detection circuit 12 detects the voltage signal from the
25 signal generating circuit 13, and outputs the signal as the output from the signal output unit 17.

The finger surface potential controller 15 has

a potential control circuit 150 which controls the potential of the high-sensitivity electrode 103. The switch SW3 of the signal generating circuit 13 and the potential control circuit 150 are together controlled by a control signal S2 input from a control signal output circuit 5a. Note that C_p in Fig. 7 denotes a parasitic capacitance.

The surface shape recognizing sensor device shown in Fig. 7 aims at solving the problem of the conventional surface shape recognizing sensor device shown in Fig. 23, and is obtained by adding the high-sensitivity electrode 103 and potential control circuit 150 to the conventional surface shape recognizing sensor device. Since the potential control circuit 150 controls the potential of the surface (a node N2) of the finger 3 via a capacitance C_c formed between the surface of the finger 3 and the high-sensitivity electrode 103, the potential at the node N2 can be controlled when a resistance R_f of the finger 3 is high because, e.g., the finger 3 is dry, thereby increasing the sensitivity of detection of the capacitance C_f .

An example of the operation of the surface shape recognizing sensor device shown in Fig. 7 when $R_f \gg 0$ will be explained below with reference to Figs. 8A to 8E.

At time t_1 in Fig. 8A, the potential of a

control signal P is changed to High level to close the switch SW1, thereby precharging the potential Vp in the node N1. On the other hand, during a period before time t2, the control signal S2 causes the switch SW3 to
5 select the power supply potential VDD, thereby setting a driving voltage Vs of the capacitive element Cs at the power supply potential VDD (Fig. 8B). After that, at time t2 in Fig. 8A, the potential of the control signal P is changed to Low level to open the switch SW1, and
10 simultaneously the control signal S2 causes the switch SW3 to select the ground potential GND, thereby lowering the driving voltage Vs of the capacitive element Cs by ΔV_s to generate a voltage signal to the detection circuit 12.

15 In the surface shape recognizing sensor device shown in Fig. 7, unlike in Fig. 25, the potential at a node N3 as the output of the potential control circuit 150 is changed in the opposite direction to the potential change at the node N1 during a period after
20 time t2 as shown in Fig. 8E, so the potential fluctuation at the node N2 after time t2 can be suppressed as shown in Fig. 8D. This makes it possible to prevent the value of the capacitance Cf from effectively decreasing, and obtain $\alpha = 1$ when Cf =
25 $\alpha \cdot C_{fr}$. Consequently, as shown in Fig. 8C, the magnitude of a difference ΔV_i between a voltage signal corresponding to a valley of the finger print and a

voltage signal corresponding to a ridge of the fingerprint can be made equal to that shown in Fig. 24C, i.e., that when the resistance R_f of the finger 3 is 0 Ω .

5 As shown in Fig. 9A, for example, the potential control circuit 150 includes a switch SW5 (setting unit) which selects a predetermined potential V1 (third potential) or V2 (fourth potential) and outputs the selected potential to the high-sensitivity
10 electrode 103. The control signal S2 used in the signal generating circuit 13 is also used as a control signal of the switch SW5, and the control signal S2 causes the switch SW5 to select the potential V1 during the period before time t_2 in Fig. 8E, and select the potential V2
15 (V1 < V2) at time t_2 . The increase in number of control signals can be prevented by using the control signal S2 for both the switches SW3 and SW5.

 As shown in Fig. 9B, for example, the potential control circuit 150 may also be formed by a
20 signal line 151 (setting unit) which supplies the control signal S2 to the high-sensitivity electrode 103. Since the potential of the control signal S2 is directly used, the potential control circuit 150 can be implemented without using any additional circuit. In
25 this arrangement, the control signal S2 has the same waveform as the potential at the node N3 shown in Fig. 8E.

Another example of the operation of the surface shape recognizing sensor device shown in Fig. 7 when $R_f \gg 0$ will be explained below with reference to Figs. 10A to 10E.

5 The basic operation is the same as the operation shown in Figs. 8A to 8E. The differences from Figs. 8A to 8E are that, as shown in Fig. 10E, the potential change at the node N3 is larger than that shown in Fig. 8E, and, as shown in Fig. 10D, the
10 potential at the node N2 transiently changes in a direction to increase at the timing of time t_2 . This makes it possible to effectively increase the value of the capacitance C_f , and obtain $\alpha > 1$ when $C_f = \alpha \cdot C_{fr}$. Consequently, as shown in Fig. 10C, the magnitude of the
15 difference ΔV_i between the voltage signal corresponding to a valley of the fingertip skin surface and the voltage signal corresponding to a ridge of the fingertip skin surface can be made larger than that shown in Fig. 24C. Since, therefore, it is readily possible to
20 determine whether the voltage signal detected by the detection circuit 12 of each sensor cell corresponds to a ridge or valley of the fingertip skin surface, ridges and valleys of the fingertip skin surface can be clearly discriminated by outputs from a plurality of sensor
25 cells.

In this embodiment as explained above, the potential control circuit 150 controls the potential of

the surface (node N2) of the finger 3 via the capacitance C_c formed between the surface of the finger 3 and the high-sensitivity electrode 103, so it is possible to control the potential at the node N2 when the resistance R_f of the finger 3 is high, and increase the sensitivity of detection of the capacitance C_f .

Note that although the potential at the node N3 is changed in accordance with the control signal S2 in this embodiment, what is important is to change the potential at the node N3 in the opposite direction to the potential change at the node N1, so the method is not limited to the use of the control signal S2, and the timing at which the potential at the node N3 is changed is not limited to the period after time t_2 .

Note also that in this embodiment, a signal obtained by storing an electric charge in the node N1 and then removing this electric charge is used as the output from the sensor cell. However, it is also possible to use, as the output from the sensor cell, a signal obtained by removing the electric charge from the node N1 and then storing an electric charge in the node N1. In this case, the potential V_p shown in Fig. 7 is set at the ground potential to allow the switch SW1 to function as a discharging circuit. In addition, the switch SW3 is caused to select the ground potential GND when the switch SW1 is closed and select the power supply potential VDD when the switch SW1 is open,

thereby storing an electric charge in the node N1. In this arrangement, if the resistance Rf is high because, e.g., the finger 3 is dry, the potential at the node N2 rises in accordance with the potential change at the node N1 when an electric charge is stored in the node N1. To prevent this, the potential control circuit 150 changes the potential at the node N3 in the opposite direction to the potential change at the node N1. That is, the potential at the node N3 is decreased. More specifically, it is only necessary to cause the switch SW5 to select the potential V2 when the switch SW1 is closed, and select the potential V1 ($V1 < V2$) when the switch SW1 is open.

[Third Embodiment]

The third embodiment of the present invention will be described below.

A surface shape recognizing sensor device according to the third embodiment of the present invention uses a potential control circuit 140a shown in Fig. 11 instead of the potential control circuit 140 shown in Fig. 2 of the first embodiment. The potential control circuit 140a includes a current source 142 which stores an electric charge in a node N3 as a connecting point between the output of the potential control circuit 140a and a high-sensitivity electrode 103, a switch SW6 which selects a predetermined potential V3 (sixth potential) or V4 (fifth potential), a switch SW7

which selects the output of the current source 142 or switch SW6, and a switch SW8 which controls an electrical connection between the output of the switch SW7 and the high-sensitivity electrode 103. The

5 switches SW6 to SW8 form a second switching element SW9.

The operation of the surface shape recognizing sensor device of this embodiment when $R_f \gg 0$ will be explained below with reference to Figs. 12A to 12E.

The basic operation is the same as the
10 operation of the first embodiment shown in Figs. 4A to 4E. The difference from Figs. 4A to 4E is the operation of the potential control circuit 140a. The switch SW6 selects the potential V4 when a control signal P is Low level, and the potential V3 ($V3 < V4$) when the control
15 signal P is High level. The switch SW7 selects the output of the switch SW6 when a control signal S1 is Low level, and the output of the current source 142 when the control signal S1 is High level. The switch SW8 is
20 turned on by a control signal E during a period before time t3 in Fig. 12B, and opened at time t3. Since the switches SW6 to SW8 thus operate, the high-sensitivity electrode 103 can be set at the potential V4 before
charging to a node N1 between the output of a signal generating circuit 11 and a sensor electrode 101 is
25 started, set at the potential V3 when the charging is started, and connected to the current source 142 to store an electric charge after the charging is

completed.

In this embodiment, it is possible not only to suppress the potential fluctuation at a node N2 during a period from time t2 to time t3 in the same manner as in Figs. 4A to 4E, but also to suppress the potential fluctuation at the node N2 at time t1 as shown in Fig. 12D by changing the potential at the node N3 in the opposite direction to the potential change at the node N1 at the charge timing of the node N1 at time t1 as shown in Fig. 12E. As a consequence, the potential at the node N2 can be controlled in all the periods, and the effective reduction in capacitance Cf caused by the potential fluctuation at the node N2 can be prevented more effectively than in the first embodiment.

In this embodiment as described above, the potential control circuit 140a controls the potential of the surface (node N2) of a finger 3 via a capacitance Cc formed between the surface of the finger 3 and the high-sensitivity electrode 103, so it is possible to control the potential at the node N2 when a resistance Rf of the finger 3 is high, and increase the sensitivity of detection of the capacitance Cf.

Note that in this embodiment, as in the first embodiment, a signal obtained by removing the electric charge from the node N1 and then storing an electric charge in the node N1 for only a predetermined time may also be output from a sensor cell. In this case, the

current source 142 is connected in the opposite direction to that shown in Fig. 11. In addition, the high-sensitivity electrode 103 is set at the potential V3 before discharging of the node N1 is started, set at the potential V4 ($V3 < V4$) when the discharging is started, and connected to the current source 142 to remove an electric charge after the discharging is completed.

[Fourth Embodiment]

10 The fourth embodiment of the present invention will be described below.

 A surface shape recognizing sensor device of the fourth embodiment of the present invention uses a potential control circuit 150a shown in Fig. 13A instead of the potential control circuit 150 shown in Fig. 7 of the second embodiment. The potential control circuit 150a has a switch SW10 (setting unit) which selects a predetermined potential V1 (eighth potential) or V2 (seventh potential, ninth potential), and outputs the selected potential to a high-sensitivity electrode 103. While the control signal S2 is used in the potential control circuit 150 shown in Fig. 9A, a control signal P is used in this embodiment. That is, in this embodiment, a switch SW1 (charging circuit) and the potential control circuit 150a are together controlled by a control signal P input from a control signal output circuit 5a.

The operation of the surface shape recognizing sensor device of this embodiment when $R_f \gg 0$ will be explained below with reference to Figs. 14A to 14E.

The basic operation is the same as the operation of the second embodiment shown in Figs. 8A to 8E. The difference from Figs. 8A to 8E is the operation of the potential control circuit 150a. The switch SW10 selects the potential V2 when the control signal P is Low level, and the potential V1 when the control signal P is High level. Since the switch SW10 thus operates, the high-sensitivity electrode 103 can be set at the potential V2 before charging to a node N1 between the output of a signal generating circuit 13 and a sensor electrode 101 is started, at the eighth potential V1 when the charging is started, and at the potential V2 after the charging is completed, thereby generating a waveform shown in Fig. 14E.

In this embodiment, it is possible not only to suppress the potential fluctuation at a node N2 during a period after time t_2 in the same manner as in Figs. 8A to 8E, but also to suppress the potential fluctuation at the node N2 at time t_1 as shown in Fig. 14D by changing the potential at the node N3 in the opposite direction to the potential change at the node N1 at the charge timing of the node N1 at time t_1 as shown in Fig. 14E. As a consequence, the potential at the node N2 can be controlled in all the periods, and the effective

reduction in capacitance C_f caused by the potential fluctuation at the node N2 can be prevented more effectively than in the second embodiment.

Note that the potential before t_1 and the
5 potential after t_2 at the node N3 are set at V_2 , but these potentials are not limited to V_2 , and the potential (seventh potential) before t_1 and the potential (ninth potential) after t_2 may also be different. In this case, another power supply is
10 prepared in addition to the potentials V_1 and V_2 shown in Fig. 13A, and control is so performed as to switch these potentials.

A potential control circuit 150b shown in Fig. 13B may also be used in place of the potential
15 control circuit 150a shown in Fig. 13A. The potential control circuit 150b has a signal line 152 (setting unit) which supplies the control signal P to the high-sensitivity electrode 103. Since the potential of the control signal P is directly used, the potential
20 control circuit 150b can be implemented without using any additional circuit.

In this embodiment as explained above, the potential control circuit 150a or 150b controls the potential of the surface (node N2) of a finger 3 via a
25 capacitance C_c formed between the surface of the finger 3 and the high-sensitivity electrode 103, so it is possible to control the potential at the node N2 when a

resistance R_f of the finger 3 is high, and increase the sensitivity of detection of the capacitance C_f .

Note that in this embodiment, as in the second embodiment, a signal obtained by removing the electric charge from the node N1 and then storing an electric charge in the node N1 may also be output from a sensor cell. In this case, as shown in Fig. 13A, for example, the high-sensitivity electrode 103 need only be set at the potential V_1 before discharging of the node N1 is started, at the potential V_2 ($V_1 < V_2$) when the discharging is started, and at the potential V_1 after the discharging is completed.

[Fifth Embodiment]

The fifth embodiment of the present invention will be described below.

In a sensor cell array according to the fifth embodiment of the present invention, sensor electrodes 101 and high-sensitivity electrodes 103 are arranged differently from Figs. 3A and 3B. That is, as shown in Fig. 15, the high-sensitivity electrode 103 is so formed as to surround the sensor electrode 101. In this arrangement, noise from an adjacent sensor cell to the sensor electrode 101 can be reduced. The arrangement shown in Fig. 15 can be applied to all the first to fourth embodiments.

[Sixth Embodiment]

The sixth embodiment of the present invention

will be described below.

In a sensor cell array according to the sixth embodiment of the present invention, sensor electrodes 101 and high-sensitivity electrodes 103 are arranged
5 differently from Figs. 3A, 3B, and 15. That is, as shown in Fig. 16, the sensor electrode 101 is so formed as to surround the high-sensitivity electrode 103. In this arrangement, the potential of the finger surface in each sensor cell can be efficiently controlled while the
10 influence from an adjacent sensor cell is reduced. The arrangement shown in Fig. 16 can be applied to all the first to fourth embodiments.

[Seventh Embodiment]

The seventh embodiment of the present
15 invention will be described below.

In a sensor cell array according to the seventh embodiment of the present invention, the formation positions of a sensor electrode and high-sensitivity electrode with respect to the substrate
20 surface are different.

Fig. 17A shows an example in which a high-sensitivity electrode 103a is formed in a position higher than a sensor electrode 101. More specifically, the sensor electrode 101 is formed on an insulating film
25 100 on a substrate, a first passivation film 102a is formed on the insulating film 100 so as to cover the sensor electrode 101, the high-sensitivity electrode

103a is formed on the first passivation film 102a, and a second passivation film 102b is formed on the first passivation film 102a so as to cover the high-sensitivity electrode 103a. The sensor electrode 101 and high-sensitivity electrode 103a are so formed as not to face each other. By using a plurality of passivation films as described above, the sensor electrode 101 and high-sensitivity electrode 103a can be easily formed at different heights.

When the high-sensitivity electrode 103a is formed in a position higher than the sensor electrode 101, the distance between the surface of a finger 3 in contact with the second passivation film 102b and the high-sensitivity electrode 103a becomes smaller than that when the sensor electrode 101 and high-sensitivity electrode 103 are formed at the same height as shown in Fig. 2 or the like. When the distance is $1/N$ ($N > 1$), for example, a capacitance C_c formed between the surface of the finger 3 and the high-sensitivity electrode 103a can be maintained even if the area of the high-sensitivity electrode 103a is $1/N$ that of the high-sensitivity electrode 103 shown in Fig. 2 or the like. That is, since the capacitance C_c can be maintained even when the high-sensitivity electrode 103a is downsized, it is possible to obtain the same effect of controlling the potential of the finger surface (node N2) as in the first to fourth embodiments. Also, when

the high-sensitivity electrode 103a is downsized as shown in Fig. 17A, it is possible to increase the area of the sensor electrode 101, and consequently increase the detection sensitivity.

5 Furthermore, as shown in Fig. 17B, a sensor electrode 101a may also be formed in a position higher than a high-sensitivity electrode 103. Referring to Fig. 17B, the high-sensitivity electrode 103 is formed on an insulating film 100 on a substrate, a first
10 passivation film 102c is formed on the insulating film 100 so as to cover the high-sensitivity electrode 103, the sensor electrode 101a is formed on the first passivation film 102c, and a second passivation film 102d is formed on the first passivation film 102c so as
15 to cover the sensor electrode 101a. The sensor electrode 101a and high-sensitivity electrode 103 are so formed as not to face each other. In this arrangement, the sensor electrode 101a can be downsized while a capacitance C_f formed between the surface of the finger
20 3 and the sensor electrode 101a is maintained. Accordingly, it is possible to increase the area of the sensor electrode 101, and consequently increase the detection sensitivity.

25 Note that in Figs. 17A and 17B, the surfaces of the passivation films 102b and 102d are desirably planarized.

Industrial Applicability

The present invention is applicable to, e.g.,
a capacitive fingerprint sensor.